ABSTRACT

A light-emitting apparatus employing a GaN-based semiconductor. The light-emitting apparatus comprises an n-type clad layer (124); an active layer (129) including an n-type first barrier layer (126), well layers (128), and second barrier layers (130); a p-type block layer (132); and a p-type clad layer (134). By setting the band gap energy Egb of the p-type block layer (132), the band gap energy Eg2 of the second barrier layers (130), the band gap energy Eg1 of the first barrier layer (126), and the band gap energy Egc of the n-type and the p-type clad layers such that the relationship $Egb > Eg2 > Eg1 \geqq Egc$ is satisfied; the carriers can be efficiently confined; and the intensity of the light emission can be increased.